

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-24. (Cancelled)

25. (New) A method for forming a silicon film, comprising:

applying a liquid material from a nozzle to a substrate, the liquid material including a silicon compound of which a chemical formula is Si_nX_{2n} , n and X representing an integer of 3 or more and a halogen atom, respectively; and

evaporating a solvent of the liquid material to form a silicon film on a part of the substrate.

26. (New) A method of forming a silicon film, comprising:

applying a liquid material from a nozzle to a substrate, the liquid material including a silicon compound having a cyclic structure, the liquid material including no silylcyclopentasilane; and

evaporating a solvent of the liquid material to form a silicon film on a part of the substrate.

27. (New) A method of forming a silicon film, comprising:

applying a liquid material from a nozzle to a substrate, the liquid material including a silicon compound having a cyclic structure, the liquid material including no silicon compound having a silyl group; and

evaporating a solvent of the liquid material to form a silicon film on a part of the substrate.

28. (New) The method of forming a silicon film according to claim 27, further comprising:

the liquid material being applied in an inert atmosphere.

29. (New) The method of forming a silicon film according to claim 27, further comprising:

the concentration of the silicon compound in the liquid material being in a range of 0.01 to 10 percent.

30. (New) The method of forming a liquid film according to claim 27, further comprising:

the silicon compound being dissolved in at least one solvent having a vapor pressure at room temperature of 0.001 to 50 mmHg.

31. (New) The method of forming a silicon film according to claim 27, further comprising:

the liquid material having a viscosity of 1 to 50 mPa·s.

32. (New) The method of forming a silicon film according to claim 27, further comprising:

the liquid material having a surface tension of 30 to 70 dyn/cm.

33. (New) The method of forming a silicon according to claim 27, further comprising:

irradiating a light to the liquid material before the evaporation of the solvent from the liquid material.

34. (New) The method of forming a silicon film according to claim 27, further comprising:

irradiating a light to the liquid material after the evaporation of the solvent from the liquid material.